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# FSA3200 —Two-Port, High-Speed USB2.0 Switch with Mobile High-Definition Link (MHL™)

## **Features**

- Low On Capacitance: 2.7 pF / 3.1 pF MHL / USB (Typical)
- Low Pow er Consumption: 30µA Maximum
- Supports MHL Rev. 2.0
- MHL Data Rate: 4.68 Gbps
- V<sub>BUS</sub> Pow ers Device with No V<sub>CC</sub>
- Packaged in 16-Lead UMLP (1.8 x 2.6 mm)
- Over-Voltage Tolerance (OVT) on all USB Ports Up to 5.25 V without External Components

## **Applications**

Cell Phones and Digital Cameras

## **Description**

The FSA3200 is a bi-directional, low-power, two-port, high-speed, USB2.0 and video data switch. Configured as a double-pole, double-throw (DPDT) switch for data and a single-pole, double-throw (SPDT) switch for ID; it is optimized for switching between high- or full-speed USB and Mobile Digital Video sources (MDV), including supporting the MHL<sup>TM</sup> Rev. 2.0 specification.

The FSA3200 contains special circuitry on the switch VO pins, for applications where the  $V_{CC}$  supply is powered off ( $V_{CC}$ =0), that allows the device to withstand an over-voltage condition. This switch is designed to minimize current consumption even when the control voltage applied to the control pins is lower than the supply voltage ( $V_{CC}$ ). This feature is especially valuable to mobile applications, such as cell phones, allowing direct interface with the general-purpose VOs of the baseband processor. Other applications include switching and connector sharing in portable cell phones, digital cameras, and notebook computers.

# **Ordering Information**

Part Number	Top Mark	Operating Temperature Range	Package
FSA3200UMX	GB	-40 to +85°C	16-Lead, Ultrathin Molded Leadless Package (UMLP), 1.8 x 2.6 mm

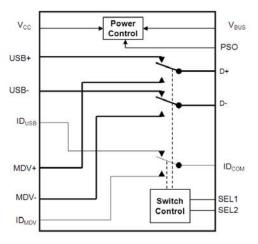


Figure 1. Analog Symbol

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## **Switch Power Operation**

In normal operation, the FSA3200 is powered from the  $V_{CC}$  pin, which typically is derived from a regulated power management device. In special circumstances, such as production test or system firmw are upgrade, the device can be powered from the  $V_{BUS}$  pin. In this mode of operation, a valid  $V_{BUS}$  voltage is present (per USB2.0 specification) and  $V_{CC}=0$  V, typically due to a no-battery condition. With the SELn pins strapped LOW (via external resistor), the FSA3200 closes the USB path, enabling the initial programming of the system directly from the USB connector. Once the system has normal

operating supply power with  $V_{CC}$  present, the  $V_{BUS}$  supply is not utilized and normal switch operation commences. Optionally, the Power Select Override (PSO) pin can be set HIGH to force the device to be powered from  $V_{BUS}$ .

The  $V_{\text{BUS}}$  /  $V_{\text{CC}}$  detection capability is not intended to be an accurate determination of the voltages present, rather a state condition detection to determine which supply should be used. These state determinations rely on the voltage conditions as described in the  $\Box$  characterization tables below.

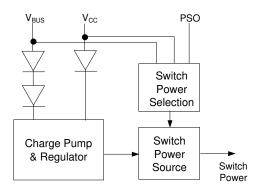


Figure 2. Simplified Logic of Switch Power Selection Circuit

Table 1. Switch Power Selection Truth Table

V <sub>cc</sub>	V <sub>BUS</sub>	PSO <sup>(1)</sup>	Switch Power Source
0	0	0	No sw itch pow er, sw itch paths high-Z
0	1	0	V <sub>BUS</sub>
1	0	0	Vcc
1	1	0	Vcc
0	0	1	No sw itch pow er, sw itch paths high-Z
0	1	1	V <sub>BUS</sub>
1	0	1	Vcc <sup>(2)</sup>
1	1	1	V <sub>BUS</sub>

#### Notes:

- 1. Control inputs should never be left floating or unconnected. If the PSO function is used, a weak pull-up resistor  $(3 \text{ M}\Omega)$  should be used to minimize static current draw. If the PSO function is not used, tie directly to GND.
- 2. PSO control is overridden with no V<sub>BUS</sub> and the power selection is switched to V<sub>CC</sub>.

Table 2. Data Switch Select Truth Table

SEL1 <sup>(3)</sup>	SEL2 <sup>(3)</sup>	Function
0	0	D+/D- connected to USB+/USB-, IDCO connected to IDusB
0	1	D+/D- connected to USB+/USB-, $ID_{COM}$ connected to $ID_{MDV}$
1	0	D+/D- connected to MDV+/MDV-, ID <sub>COM</sub> connected to ID <sub>USB</sub>
1	1	D+/D- connected to MDV+/MDV-, ID <sub>COM</sub> connected to ID <sub>MDV</sub>

#### Note:

3. Control inputs should never be left floating or unconnected. To guarantee default sw itch closure to the USB position, the SEL pins should be tied to GND with a weakpull- down resistor ( $3\,\mathrm{M}\Omega$ ) to minimize static current draw .

# **Pin Configuration**

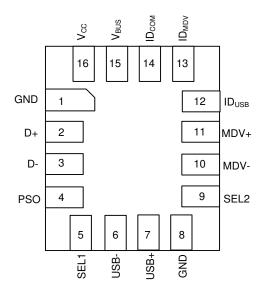


Figure 3. Pin Assignments (Top-Through View)

## **Pin Definitions**

Pin#	Name	Description
1	GND	Ground
2	D+	Data Switch Output (Positive)
3	D-	Data Switch Output (Negative)
4	PSO	Pow er Select Override
5	SEL1	Data Switch Select
6	USB-	USB Differential Data (Negative)
7	USB+	USB Differential Data (Positive)
8	GND	Ground
9	SEL2	ID Sw itch Select
10	MDV-	MDV Differential Data (Negative)
11	MDV+	MDV Differential Data (Positive)
12	ID <sub>USB</sub>	ID Switch MUX Output for USB
13	ID <sub>MDV</sub>	ID Switch MUX Output for MDV
14	ID <sub>COM</sub>	ID Switch Common
15	V <sub>BUS</sub>	Device Power when V <sub>CC</sub> Not Available
16	V <sub>CC</sub>	Device Power from System <sup>(4)</sup>

## Note:

4. Device automatically switches from  $V_{BUS}$  when valid  $V_{CC}$  minimum voltage is present.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter			Max.	Unit
V <sub>CC</sub> , V <sub>BUS</sub>	Supply Voltage		-0.5	5.5	V
V <sub>CNTRL</sub>	DC Input Voltage (SELn, PSO) <sup>(5)</sup>		-0.5	Vcc	V
V <sub>SW</sub> <sup>(6)</sup>	DC Switch I/O Voltage <sup>(5)</sup>		-0.50	5.25	V
lık	DC Input Diode Current		-50		mA
ЮПТ	DC Output Current			100	mA
T <sub>STG</sub>	Storage Temperature		-65	+150	°C
MSL	Moisture Sensitivity Level (JEDEC J-STD-020A)			1	
	Human Body Model, JEDEC: JESD22-A114	All Pins		3.5	
ESD	IEC 61000-4-2, Level 4, for D+/D- and V <sub>CC</sub> Pins <sup>(7)</sup>	Contact		8.0	kV
ESD	IEC 61000-4-2, Level 4, for D+/D- and V <sub>CC</sub> Pins <sup>(7)</sup>	Air		15.0	r.v
	Charged Device Model, JESD22-C101	•		2.0	

#### Notes:

- 5. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
- V<sub>SW</sub> refers to analog data sw itch paths (USB, MDV, and ID).
- 7. Testing performed in a system environment using TVS diodes.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>BUS</sub>	Supply Voltage Running from V <sub>BUS</sub> Voltage	4.20	5.25	V
Vcc	Supply Voltage Running from V <sub>CC</sub>	2.7	4.5	V
tramp(vbus)	Pow er Supply Slew Rate from V <sub>BUS</sub>	100	1000	μs/V
t <sub>RAMP(VCC)</sub>	Pow er Supply Slew Rate from V <sub>CC</sub>	100	1000	μs/V
$\Theta_{JA}$	Thermal Resistance		336	C°/W
V <sub>CNTRL</sub>	Control Input Voltage (SELn, PSO) <sup>(8)</sup>	0	4.5	V
V <sub>SW(USB)</sub>	Switch I/O Voltage (USB and ID Switch Paths)	-0.5	3.6	V
V <sub>SW(MDV)</sub>	Switch I/O Voltage (MDV Switch Path)	1.65	3.45	V
T <sub>A</sub>	Operating Temperature	-40	+85	°C

#### Note:

8. The control inputs must be held HIGH or LOW; they must not float.

# **DC Electrical Characteristics**

All typical value are at  $T_A=25^{\circ}C$  unless otherwise specified.

Comphal	Davamatav	Oo maliki o m	V 00	T <sub>A</sub> =- 4	10ºC to	+85ºC	Unit
Symbol	Parameter	Condition	V <sub>cc</sub> (V)	Min.	Тур.	Max.	Unit
V <sub>IK</sub>	Clamp Diode Voltage	I <sub>IN</sub> =-18 mA	2.7			-1.2	V
V <sub>IH</sub>	Control Input Voltage High	SELn, PSO	2.7 to 4.3	1.25			V
VıL	Control Input Voltage Low	SELn, PSO	2.7 to 4.3			0.6	٧
lιΝ	Control Input Leakage	V <sub>SW</sub> =0 V to 3.6 V, V <sub>CNTRL</sub> =0 V to 1.98 V	4.3	-1		1	μΑ
loz(MDV)	Off-State Leakage for Open MDV Data Paths	$V_{SW}$ =1.65 $V \le MDV$ $\le 3.45 V$	4.3	-1		1	μΑ
loz(USB)	Off-State Leakage for Open USB Data Paths	$V_{SW}=0$ $V \le USB \le 3.6$ $V$	4.3	-1		1	μΑ
loz(ID)	Off-State Leakage for Open ID Data Path	$V_{SW}=0$ $V \le ID \le 3.6$ $V$	4.3	-0.5		0.5	μΑ
ICL(MDV)	On-State Leakage for Closed MDV Data Paths <sup>(9)</sup>	$\begin{array}{l} V_{SW} \!\!=\! 1.65 \ V \leq \ MDV \\ \leq 3.45 \ V \end{array}$	4.3	-1		1	μΑ
I <sub>CL(USB)</sub>	On-State Leakage for Closed USB Data Paths (9)	$V_{SW}=0$ $V \le USB \le 3.6$ $V$	4.3	-1		1	μΑ
I <sub>CL(ID)</sub>	On-State Leakage for Closed <sup>(9)</sup> ID Data Path	$V_{SW}=0$ $V \le ID \le 3.6$ $V$	4.3	-0.5		0.5	μΑ
loff	Pow er-Off Leakage Current (All I/O Ports)	V <sub>SW</sub> =0 V or 3.6 V, Figure 5	0	-1		1	μА
R <sub>ON(USB)</sub>	HS Switch On Resistance (USB to D Path)	V <sub>SW</sub> =0.4 V, l <sub>ON</sub> =-8 mA Figure 4	2.7		3.9	6.5	Ω
RON(MDV)	HS Switch On Resistance (MDV to D Path)	V <sub>SW</sub> =V <sub>CC</sub> -1050mV, I <sub>ON</sub> =-8mA, Figure 4	2.7		5		Ω
R <sub>ON(ID)</sub>	LS Switch On Resistance (ID Path)	V <sub>SW</sub> =3V, l <sub>ON</sub> =-8mA Figure 4	2.7		12		Ω
$\Delta R_{ON(MDV)}$	Difference in R <sub>ON</sub> Between MDV Positive-Negative	V <sub>SW</sub> =V <sub>CC</sub> -1050 mV, I <sub>ON</sub> =-8 mA, Figure 4,	2.7		0.03		Ω
$\Delta R_{ON(USB)}$	Difference in R <sub>ON</sub> Between USB Positive-Negative	V <sub>SW</sub> =0.4 V, l <sub>ON</sub> =-8 mA Figure 4	2.7		0.18		Ω
$\Delta R_{ON(ID)}$	Difference in R <sub>ON</sub> Between ID Sw itch Paths	V <sub>SW</sub> =3 V, I <sub>ON</sub> =-8 mA Figure 4	2.7		0.4		Ω
Ronf(MDV)	Flatness for R <sub>ON</sub> MDV Path	V <sub>SW</sub> =1.65 V to 3.45 V, l <sub>ON</sub> =-8 mA, Figure 4	2.7		1		Ω
lvbus	V <sub>BUS</sub> Quiescent Current	V <sub>BUS</sub> =5.25 V, V <sub>CNTRL</sub> =0 V or 1.98 V, l <sub>OUT</sub> =0	4.3			100	μΑ
lcc	V <sub>CC</sub> Quiescent Current	V <sub>BUS</sub> =0 V, V <sub>CNTRL</sub> =0 V or 1.98 V, l <sub>OUT</sub> =0	4.3			30	μΑ

#### Note:

9. For this test, the data switch is closed with the respective switch pin floating.

# **AC Electrical Characteristics**

All typical value are for  $V_{\text{CC}}$ =3.3 V and  $T_{\text{A}}$ =25°C unless otherwise specified.

Cymbol	Parameter	Condition	v (M)	T <sub>A</sub> =- 4	0ºC to	+85ºC	Unit
Symbol	Parameter	Condition	V <sub>CC</sub> (V)	Min.	Тур.	Max.	Unit
t <sub>ON</sub>	Turn-On Time, SELn to Output	R <sub>L</sub> =50 $\Omega$ , C <sub>L</sub> =5 pF, V <sub>SW(USB)</sub> =0.8 V, V <sub>SW(MDV)</sub> =3.3 V, Figure 6, Figure 7	2.7 to 3.6		445	600	ns
toff	Turn-Off Time, SELn to Output	$\begin{array}{l} R_L \!\!=\!\! 50 \;\; \Omega, \; C_L \!\!=\!\! 5 \;\; pF, \\ V_{SW(USB)} \!\!=\!\! 0.8 \; V, \; V_{SW(MDV)} \!\!=\!\! 3.3 V, \\ Figure \;\; 6, \; Figure \;\; 7 \end{array}$	2.7 to 3.6		125	300	ns
t <sub>PD</sub>	Propagation Delay <sup>(10)</sup>	$C_L=5$ pF, $R_L=50$ $\Omega$ , Figure 6, Figure 8	2.7 to 3.6		0.25		ns
t <sub>BBM</sub>	Break-Before-Make <sup>(10)</sup>	$\begin{array}{l} \text{R}_\text{L}\text{=}50 \;\; \Omega , \; \text{C}_\text{L}\text{=}5 \;\; \text{pF}, \\ \text{V}_\text{ID}\text{=}\text{V}_\text{MDV}\text{=}3.3 \; \text{V}, \; \text{V}_\text{USB}\text{=}0.8 \; \text{V}, \\ \text{Figure} \;\; 10 \end{array}$	2.7 to 3.6	2.0		13	ns
O <sub>IRR(MDV)</sub>	Off Isolation <sup>(10)</sup>	$V_{S}$ =1 $V_{pk\cdot pk}$ , $R_{L}$ =50 $\Omega$ , f=240 MHz, Figure 12	2.7 to 3.6		-45		dB
OIRR(USB)	On solution	$V_S$ =400m $V_{pk\cdot pk}$ , $R_L$ =50 $\Omega$ , f=240MHz, Figure 12	2.7 to 3.6		-38		dB
Xtalk <sub>MDV</sub>	Non-Adjacent Channel <sup>(10)</sup>	$V_{S}$ =1 $V_{pk\cdot pk}$ , $R_{L}$ =50 $\Omega$ , f=240 MHz, Figure 13	2.7 to 3.6		-44		dB
Xtalk <sub>USB</sub>	Crosstalk	$V_S$ =400 mV $_{pk,pk}$ , RL=50 $\Omega$ , f=240 MHz, Figure 13	2.7 to 3.6		-39		dB
		V <sub>IN</sub> =1 V <sub>pk-pk</sub> , MDV Path, R <sub>L</sub> =50 Ω, C <sub>L</sub> =0 pF, Figure 11, Figure 16			2.34		GHz
BW	BW Differential -3 db Bandw idth <sup>(10)</sup>	$V_{IN}$ =400 m $V_{pk-pk}$ , USB Path, $R_L$ =50 $\Omega$ , $C_L$ =0 pF, Figure 11, Figure 17	2.7 to 3.6		1.59		5
		ID Path, $R_L$ =50 $\Omega$ , $C_L$ =0 pF, Figure 11			100		MHz

## Note:

10. Guaranteed by characterization.

# **USB High-Speed AC Electrical Characteristics**

Typical values are at  $T_A = -40^{\circ} C$  to  $+85^{\circ} C$ .

Symbol	Parameter	Condition	V <sub>cc</sub> (V)	Тур.	Unit
tsk(P)	Skew of Opposite Transitions of the Same Output <sup>(11)</sup>	C <sub>L</sub> =5 pF, R <sub>L</sub> =50 $\Omega$ , Figure 9	3.0 to 3.6	3	ps
tJ	Total Jitter <sup>(11)</sup>	$R_L$ =50 Ω, $C_L$ =5 pf, $t_R$ = $t_F$ =500 ps (10-90%) at 480 Mbps, PN7	3.0 to 3.6	15	ps

## Note:

11. Guaranteed by characterization.

## **MDV AC Electrical Characteristics**

Typical values are at  $T_A = -40^{\circ} C$  to  $+85^{\circ} C$ .

Symbol	Parameter	Condition	V <sub>cc</sub> (V)	Тур.	Unit
t <sub>SK(P)</sub>	Skew of Opposite Transitions of the Same Output (12)	R <sub>PU</sub> =50 $\Omega$ to V <sub>CC</sub> , C <sub>L</sub> =0 pF	3.0 to 3.6	3	ps
tu	Total Jitter <sup>(12)</sup>	f=2.25 Gbps, PN7, R <sub>PU</sub> =50 $\Omega$ to V <sub>CC</sub> , C <sub>L</sub> =0 pF	3.0 to 3.6	15	ps

## Note:

12. Guaranteed by characterization.

# Capacitance

Typical values are at  $T_A = -40^{\circ} C$  to  $+85^{\circ} C$ .

Symbol	Parameter	Condition	Тур.	Unit
C <sub>IN</sub>	Control Pin Input Capacitance (13)	V <sub>CC</sub> =0 V, f= 1 MHz	1.5	
C <sub>ON(USB)</sub>	USB Path On Capacitance (13)	V <sub>CC</sub> =3.3 V,f=240 MHz, Figure 15	3.1	
Coff(USB)	USB Path Off Capacitance (13)	V <sub>CC</sub> =3.3 V, f=240 MHz, Figure 14	1.6	pF
C <sub>ON(MDV)</sub>	MDV Path On Capacitance (13)	V <sub>CC</sub> =3.3 V,f=240 MHz, Figure 15	2.7	
Coff(MDV)	MDV Path Off Capacitance (13)	V <sub>CC</sub> =3.3 V, f=240 MHz, Figure 14	1.1	

## Note:

13. Guaranteed by characterization.

# **Test Diagrams**

#### Note:

14. HSD refers to the high-speed data USB or MDV paths.

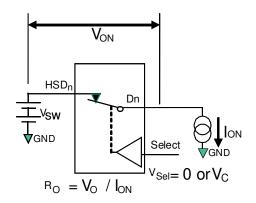
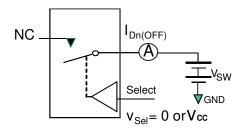
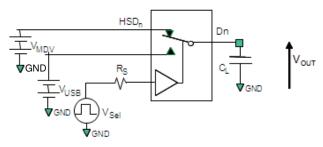


Figure 4. On Resistance



\*\*Each switch port is tested separately

Figure 5. Off Leakage



 $R_S$ , and  $C_L$  are functions of the application environment (see AC Tables for specific values)  $C_L$  includes test fixture and stray capacitance.

Figure 6. AC Test Circuit Load

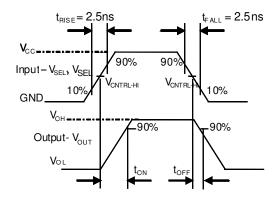


Figure 7. Turn-On / Turn-Off Waveforms

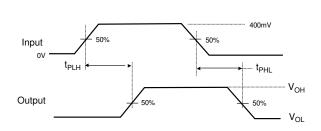


Figure 8. Propagation Delay (t<sub>R</sub>t<sub>F</sub> – 500 ps)

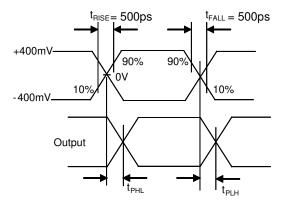


Figure 9. Intra-Pair Skew Test t<sub>SK(P)</sub>

# Test Diagrams (Continued)

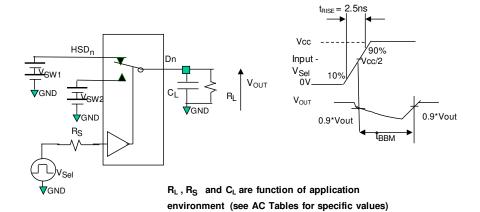
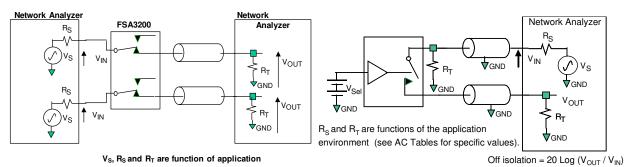


Figure 10. Break-Before-Make Interval Timing

C<sub>L</sub> includes test fixture and stray capacitance



V<sub>S</sub>, R<sub>S</sub> and R<sub>T</sub> are function of application environment (see AC/DC Tables for values)

Figure 11. Insertion Loss

Figure 12. Channel Off Isolation

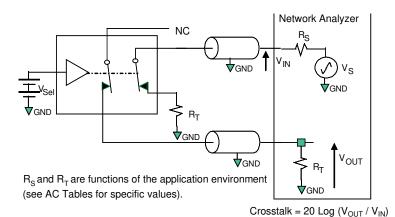


Figure 13. Non-Adjacent Channel-to-Channel Crosstalk

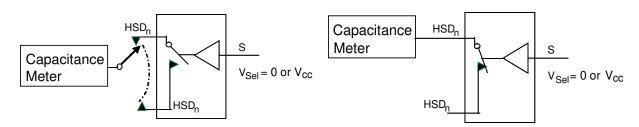


Figure 14. Channel Off Capacitance

Figure 15. Channel On Capacitance

## **Insertion Loss**

One of the key factors for using the FSA3200 in mobile digital video applications is the small amount of insertion loss experienced by the received signal as it passes through the switch. This results in minimal degradation of the received eye. One of the ways to measure the quality of the high data rate channels is using balanced

ports and 4-port differential S-parameter analysis, particularly SDD21.

Bandwidth is measured using the S-parameter SDD21 methodology. Figure 16 shows the bandwidth (GHz) for the MDV path and Figure 17 the bandwidth curve for the USB path.

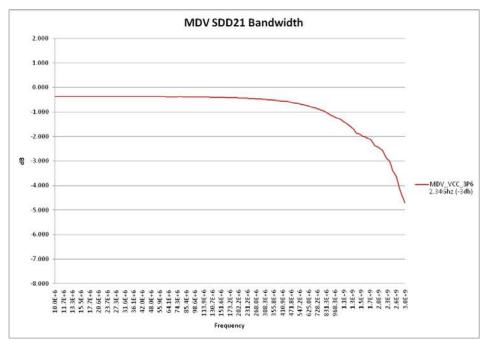


Figure 16. MDV Path SDD21 Insertion Loss Curve

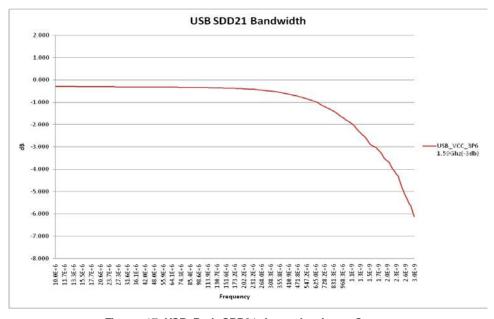


Figure 17. USB Path SDD21 Insertion Loss Curve

# **Typical Applications**

Figure 18 shows the FSA3200 utilizing the  $V_{\hbox{\scriptsize BUS}}$  connection from the micro-USB connector. The 3M resistor is used to ensure, for manufacturing test via the micro-USB connector, that the FSA3200 configures for

connectivity through the FSA9280A accessory switch. Figure 19 shows the configuration for the FSA3200 "self pow ered" by the battery only.

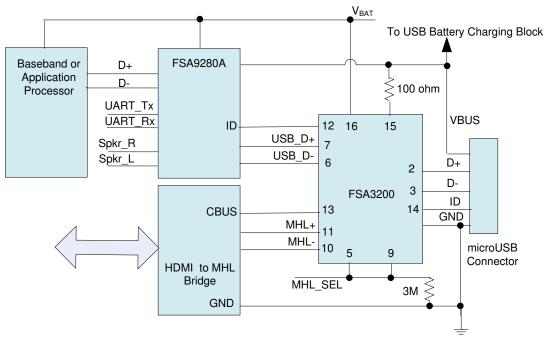


Figure 18. Typical FSA3200 Application Using V<sub>BUS</sub>

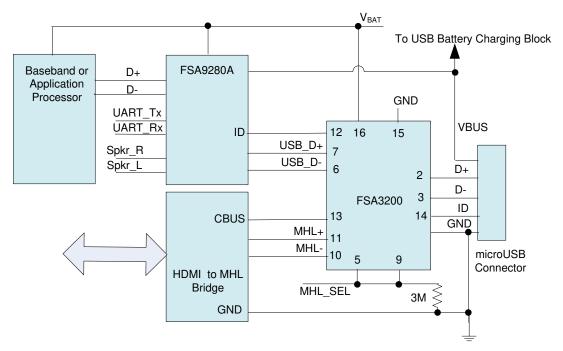
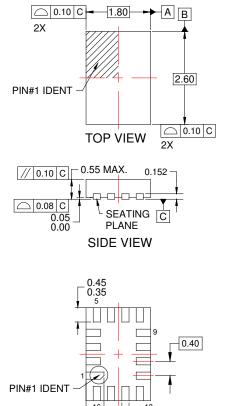


Figure 19. Typical FSA3200 "Self-Powered" Application Using VBAT

# **Physical Dimensions**





A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC STANDARD.

**BOTTOM VIEW** 

0.10 C A B

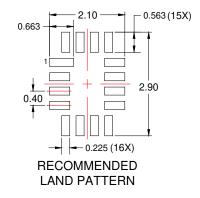
0.05 C

 $\Phi$ 

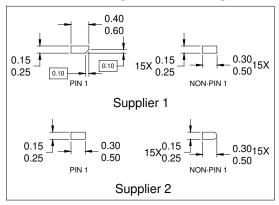
B. DIMENSIONS ARE IN MILLIMETERS.

0.55 0.45

- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
- E. DRAWING FILENAME: MKT-UMLP16Arev4.
- F. TERMINAL SHAPE MAY VARY ACCORDING TO PACKAGE SUPPLIER, SEE TERMINAL SHAPE VARIANTS.



#### TERMINAL SHAPE VARIANTS



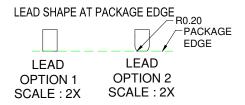


Figure 20. 16-Lead, Ultrathin Molded Leadless Package (UMLP)

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